

30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS}$ =-30V; $R_{DS(ON)}$ =0.35 Ω ; I_D =-1.1A

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC DC converters
- Power management functions
- Disconnect switches
- Motor control

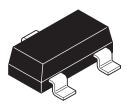
ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL	
ZXM61P03FTA	7	8 embossed	3,000	
ZXM61P03FTC	13	8 embossed	10,000	

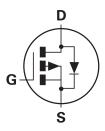
DEVICE MARKING

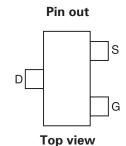
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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-30	V
Gate- Source Voltage	V _{GS}	±20	V
Continuous Drain Current $(V_{GS}=-10V; T_A=25^{\circ}C)(b) \ (V_{GS}=-10V; T_A=70^{\circ}C)(b)$	I _D	-1.1 -0.9	А
Pulsed Drain Current (c)	I _{DM}	-4.3	А
Continuous Source Current (Body Diode)(b)	I _S	-0.88	А
Pulsed Source Current (Body Diode)(c)	I _{SM}	-4.3	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	625 5	m₩ mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

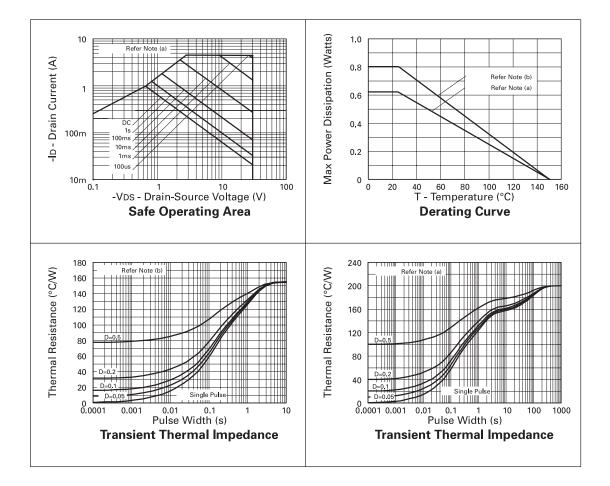
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	155	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.





CHARACTERISTICS



PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
STATIC	1	1			1	1	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} =-30V, V _{GS} =0V	
Gate-Body Leakage	I _{GSS}			±100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.35 0.55	Ω Ω	V _{GS} =-10V, I _D =-0.6A V _{GS} =-4.5V, I _D =-0.3A	
Forward Transconductance (3)	g _{fs}	0.44			S	V _{DS} =-10V,I _D =-0.3A	
DYNAMIC (3)	•			•			
Input Capacitance	C _{iss}		140		pF		
Output Capacitance	C _{oss}		45		pF	V _{DS} =-25 V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		20		pF		
SWITCHING(2) (3)	•						
Turn-On Delay Time	t _{d(on)}		1.9		ns		
Rise Time	t _r		2.9		ns	V _{DD} =-15V, I _D =-0.6A	
Turn-Off Delay Time	t _{d(off)}		8.9		ns	$R_G = 6.2\Omega, R_D = 25\Omega$ (Refer to test circuit)	
Fall Time	t _f		5.0		ns		
Total Gate Charge	Qg			4.8	nC		
Gate-Source Charge	Q _{gs}			0.62	nC	V _{DS} =-24V,V _{GS} =-10V, I _D =-0.6A	
Gate Drain Charge	Q _{gd}			1.3	nC	(Refer to test circuit)	
SOURCE-DRAIN DIODE	,				•	•	
Diode Forward Voltage (1)	V _{SD}			-0.95	V	T _j =25°C, I _S =-0.6A, V _{GS} =0V	
Reverse Recovery Time (3)	t _{rr}		14.8		ns	$T_{i}=25^{\circ}C, I_{F}=-0.6A,$	
Reverse Recovery Charge(3)	Q _{rr}		7.7		nC	di/dt= 100A/μs	

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

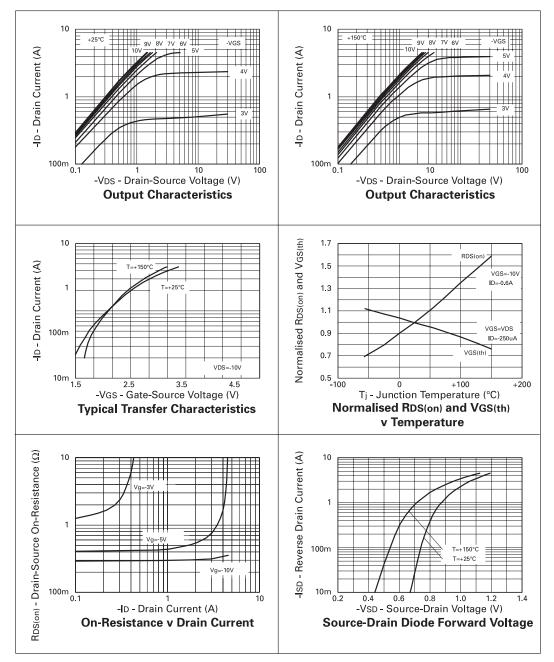
NOTES:

(1) Measured under pulsed conditions. Width=300 $\mu s.$ Duty cycle ${\leq}2\%.$

(2) Switching characteristics are independent of operating junction temperature.

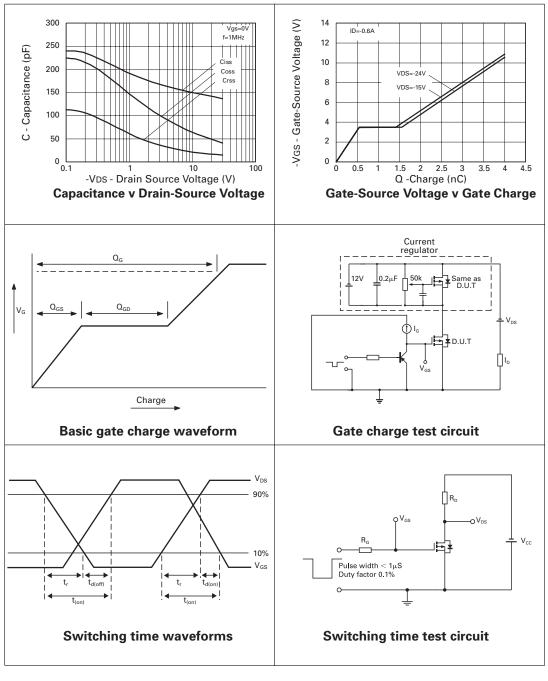
(3) For design aid only, not subject to production testing.





TYPICAL CHARACTERISTICS

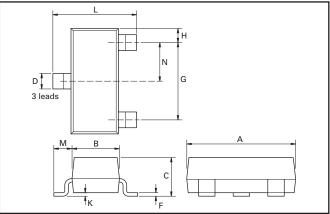


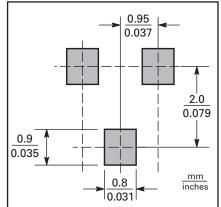


TYPICAL CHARACTERISTICS



PACKAGE DETAILS





PAD LAYOUT DETAILS

PACKAGE DIMENSIONS

	Millin	neters	Inc	hes		Millimeters		Inches	
DIM	Min	Max	Min	Max	DIM	Min	Max	Мах	Max
А	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	К	0.01	0.10	0.0004	0.004
С	_	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	М	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90	NOM	0.075	NOM	—	—			

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH	Zetex Inc	Zetex (Asia) Ltd	Zetex Semiconductors plc
Streitfeldstraße 19	700 Veterans Memorial Hwy	3701-04 Metroplaza Tower 1	Zetex Technology Park
D-81673 München	Hauppauge, NY 11788	Hing Fong Road, Kwai Fong	Chadderton, Oldham, OL9 9LL
Germany	USA	Hong Kong	United Kingdom
Telefon: (49) 89 45 49 49 0	Telephone: (1) 631 360 2222	Telephone: (852) 26100 611	Telephone (44) 161 622 4444
Fax: (49) 89 45 49 49	Fax: (1) 631 360 8222	Fax: (852) 24250 494	Fax: (44) 161 622 4446
<u>europe.sales@zetex.com</u>	<u>usa.sales@zetex.com</u>	<u>asia.sales@zetex.com</u>	hq@zetex.com

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